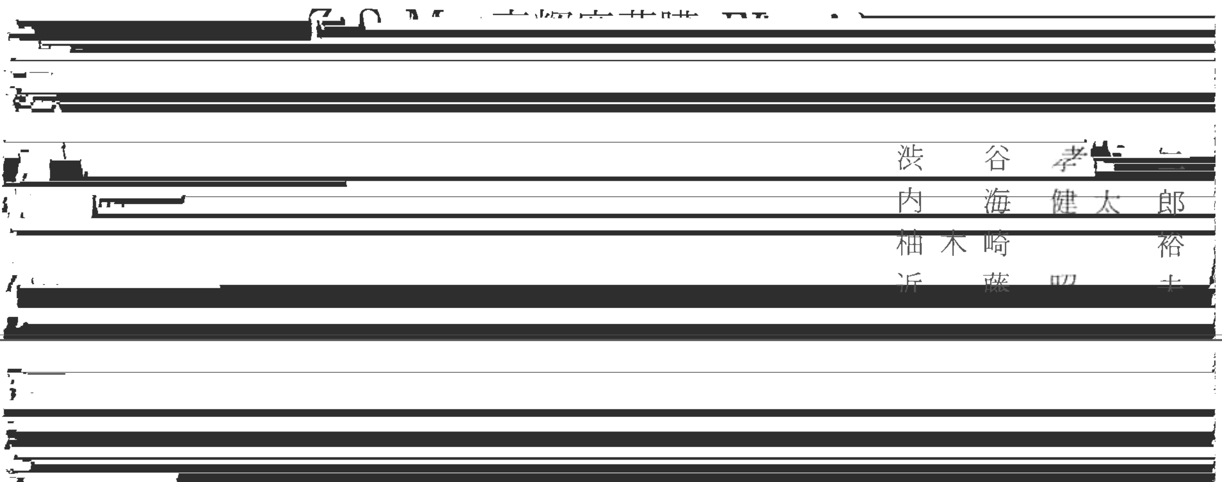
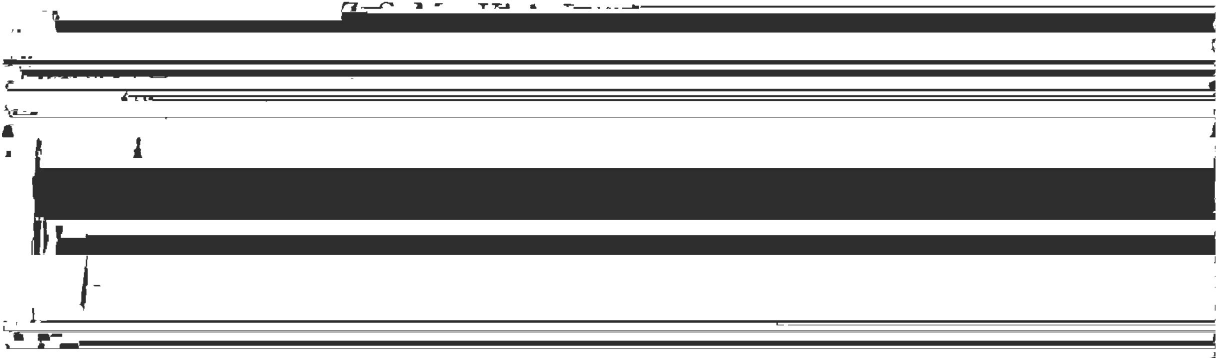
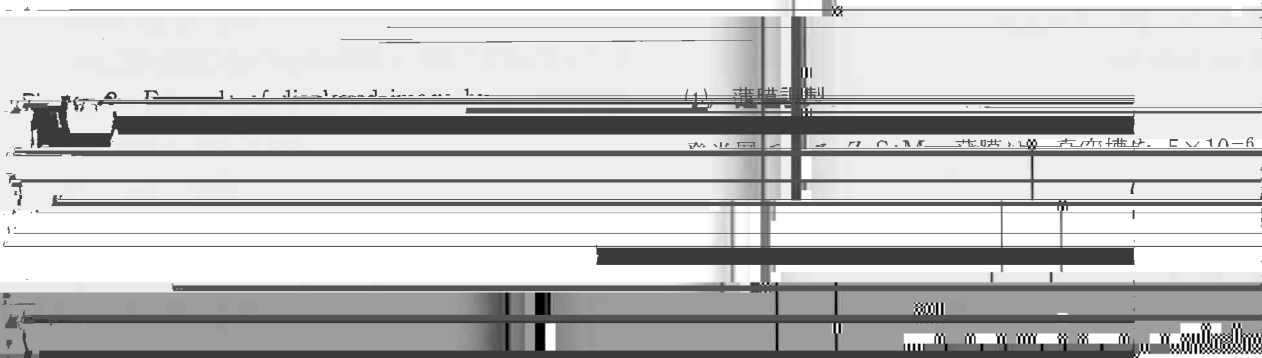


渋谷孝

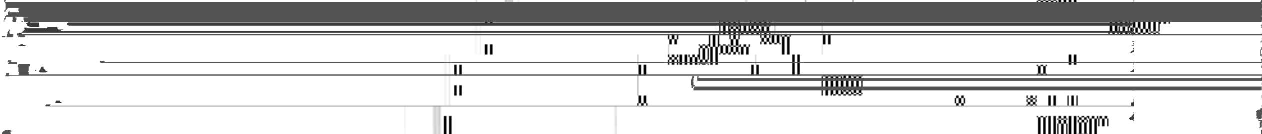
内海健太郎

柚木崎裕

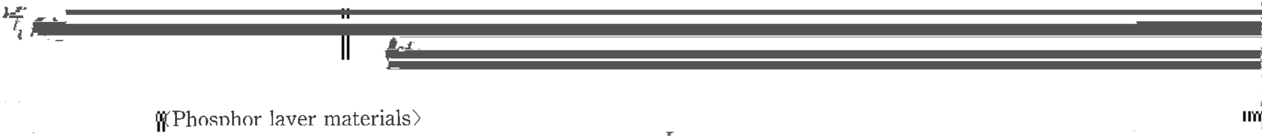




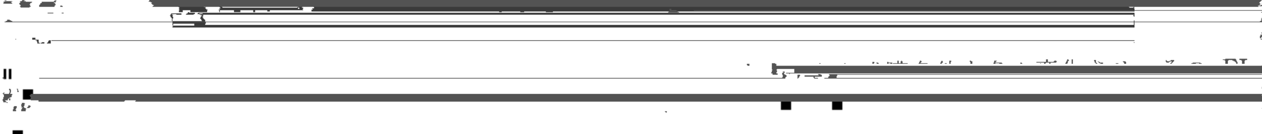
(1) 薄膜調製

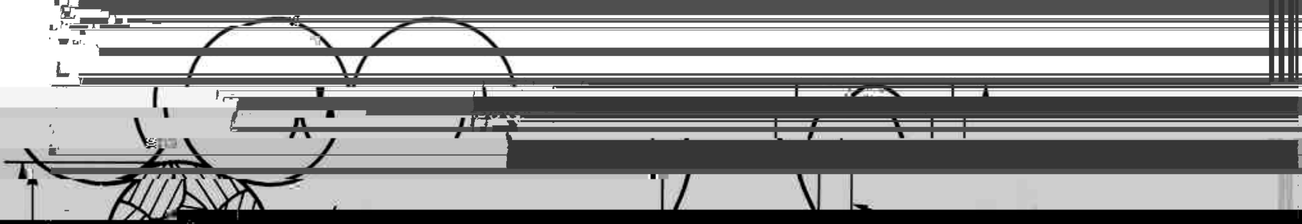


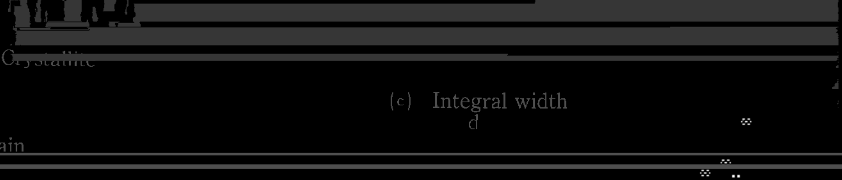
diagonal EL panel



〈Phosphor layer materials〉







$B_i = \frac{I_N}{I_P}$

(c) Integral width

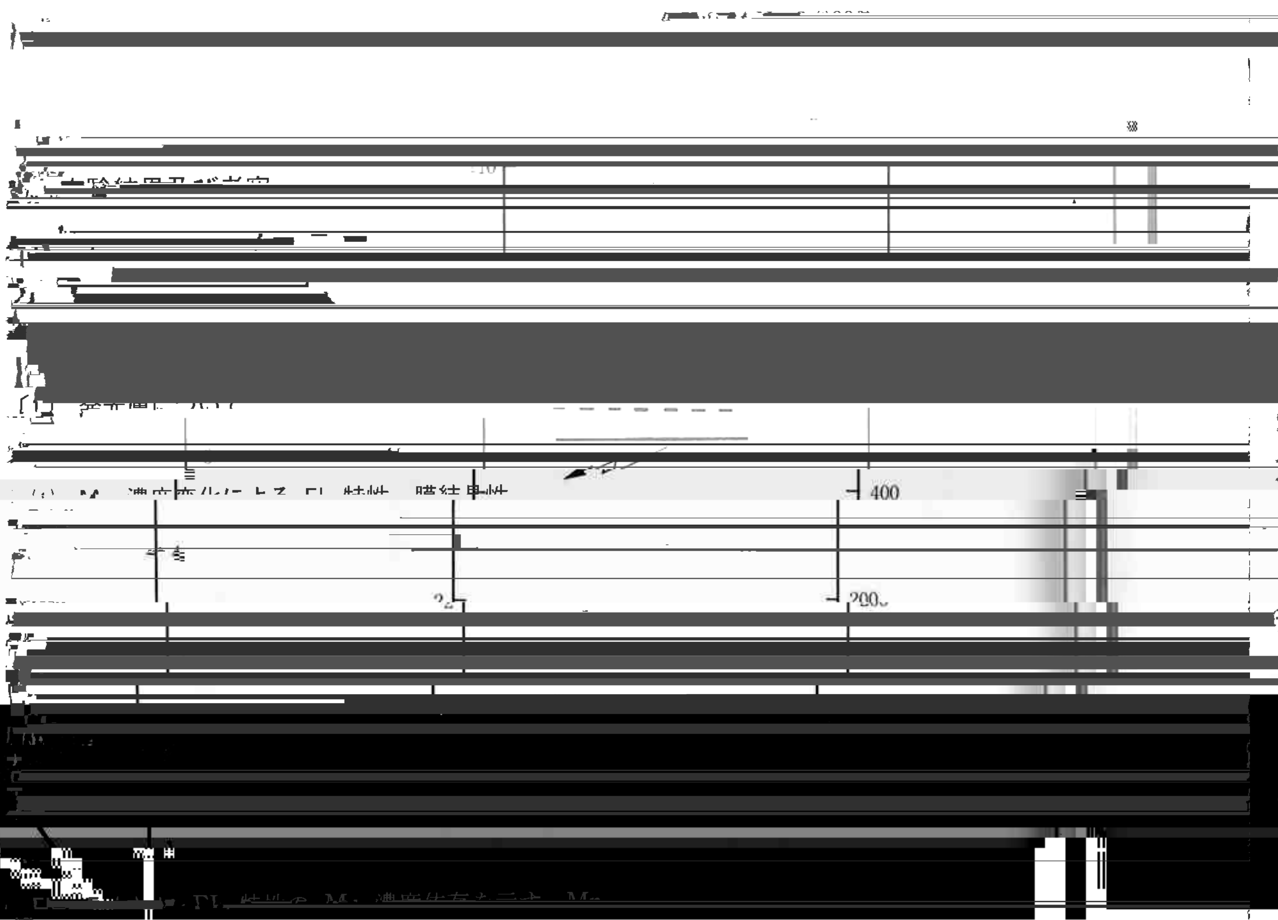
(a) Crystallite and grain

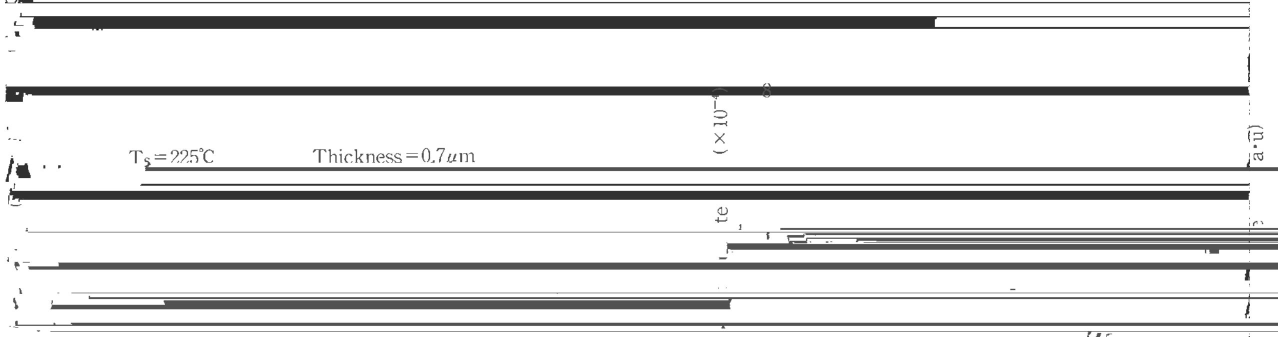
Table 1 Sputtering condition for insulating layers

Condition

1. None-alkali glass

2. ITO or Al electrode





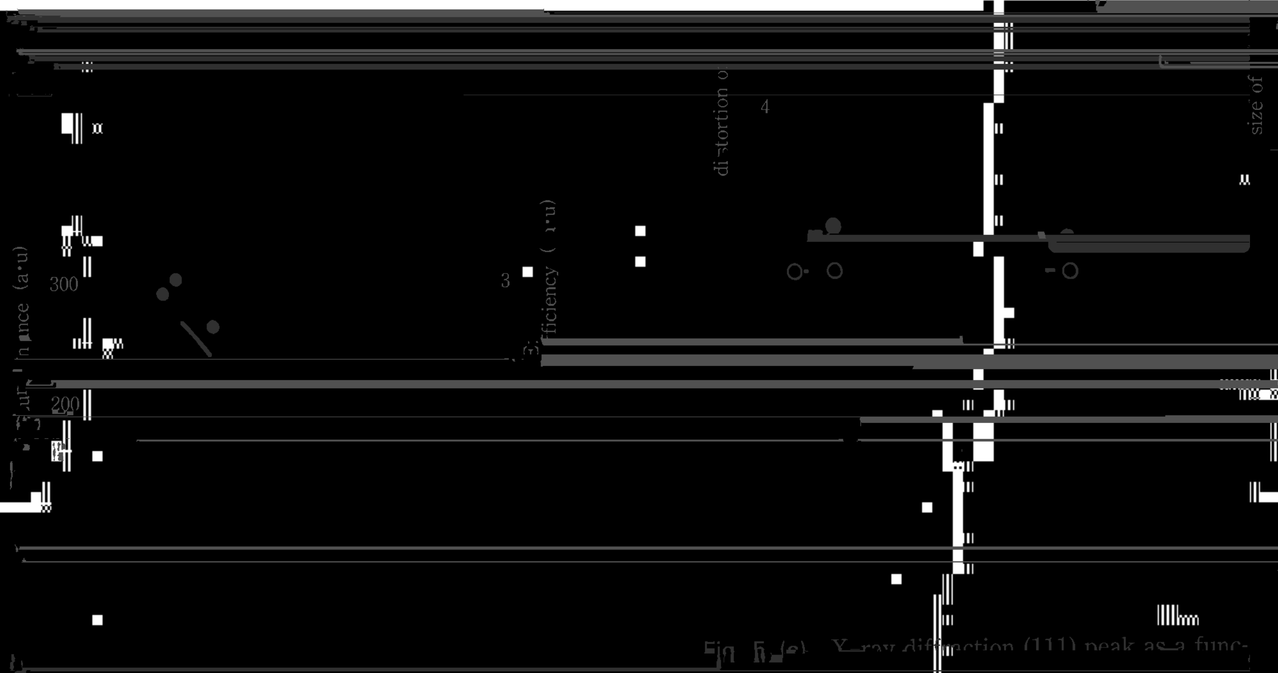
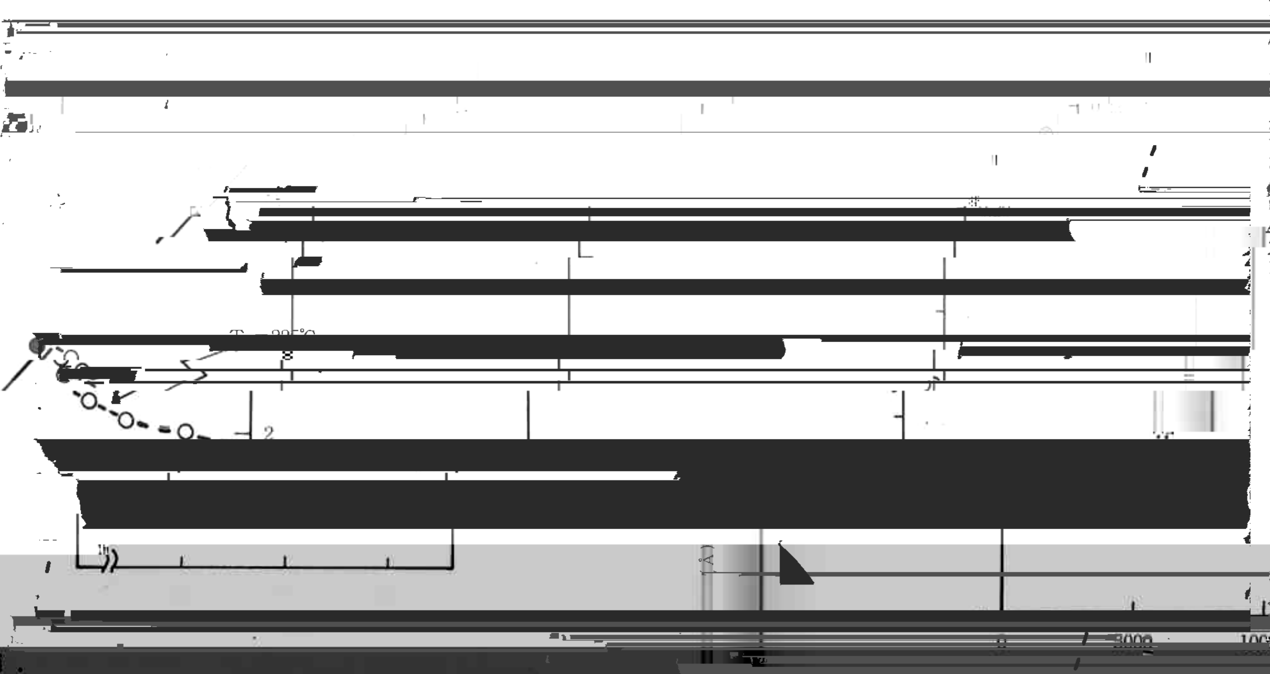


Fig. 5 (a) X-ray diffraction (111) peak as a func-

濃度が 0.5~0.6 wt%の狭い範囲に輝度，効率とも最適



150
200
250
T S (℃)

0 16
0 14
15000

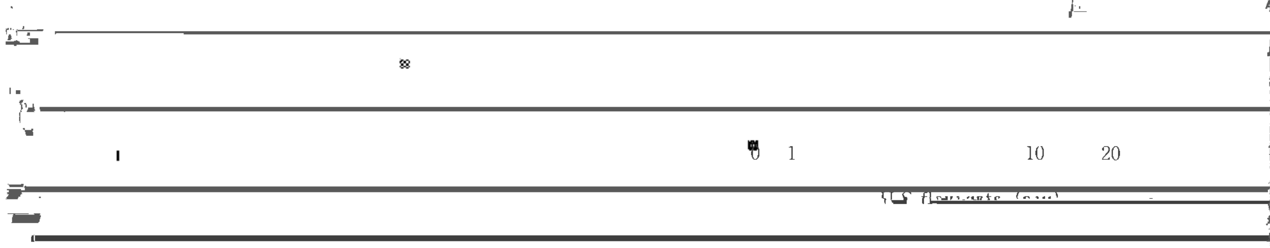


Fig. 8 (b) X-ray diffraction ([illegible]) peak as a func-

Fig. 10

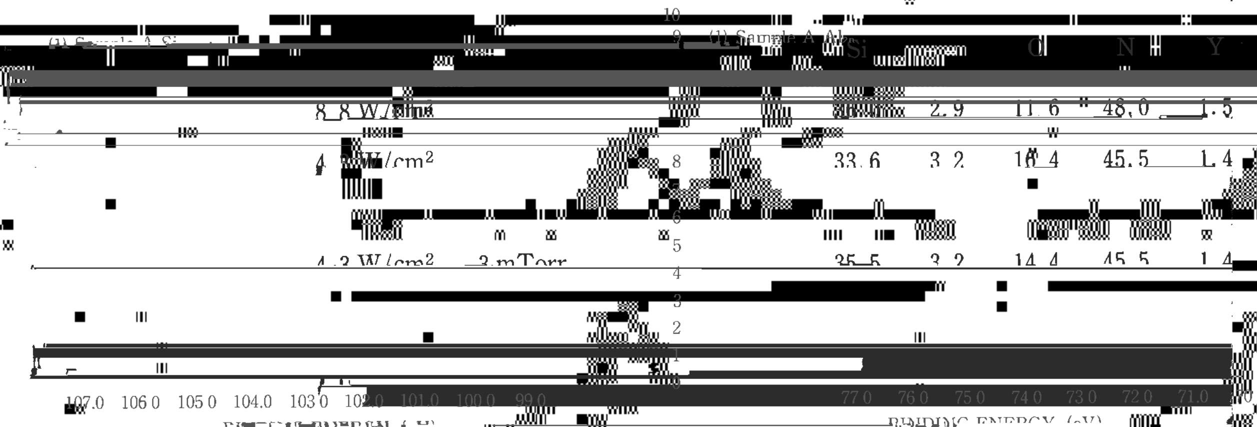
Fig. 12 Dielectric constant of SiAlON as a function of preparation condition

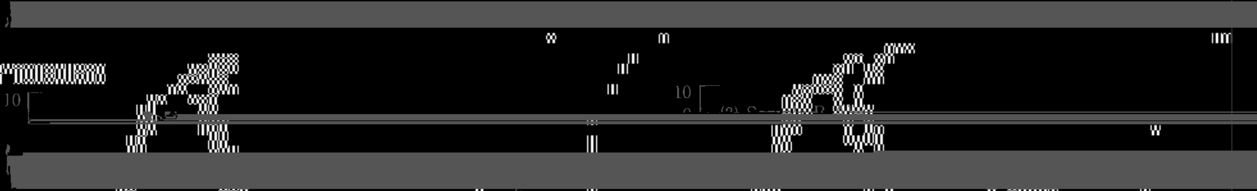
Table 2 Preparation condition of SiAlON

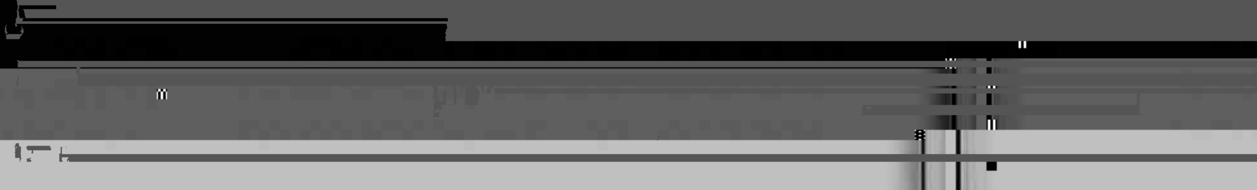
Sample	Condition	
A	8.8 W/cm²	[illegible]
B	4.[illegible] W/cm²	[illegible]
C	4.3 W/cm²	3 mTorr

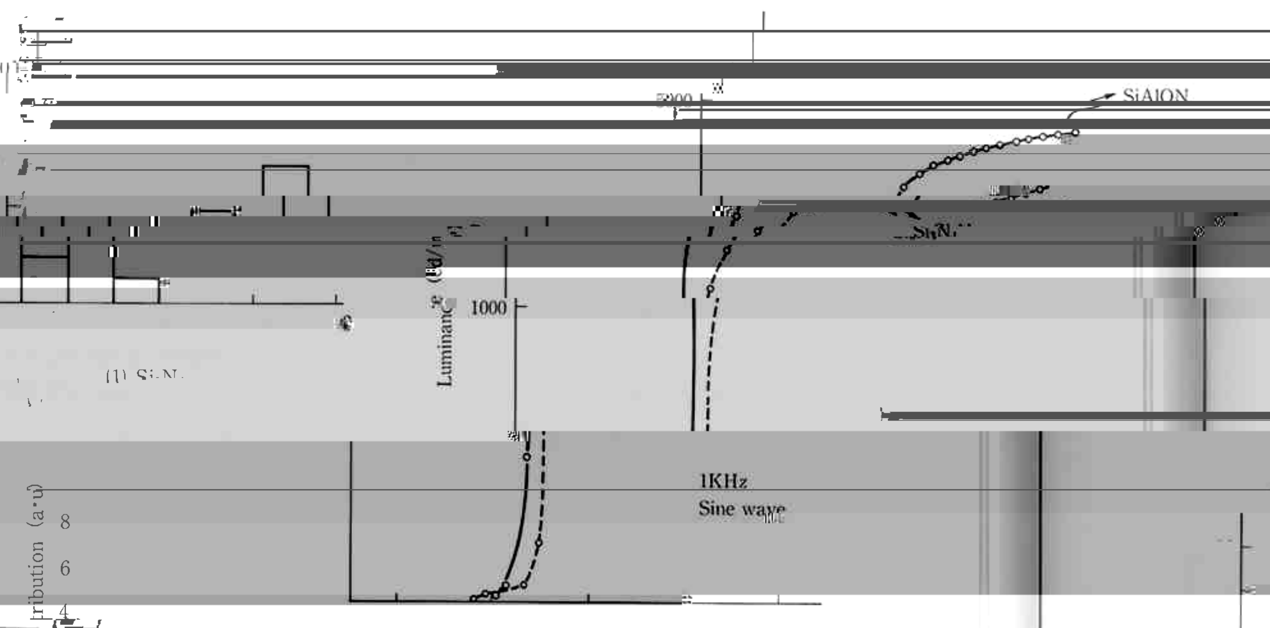
Table 3 EPMA results of SiAlON

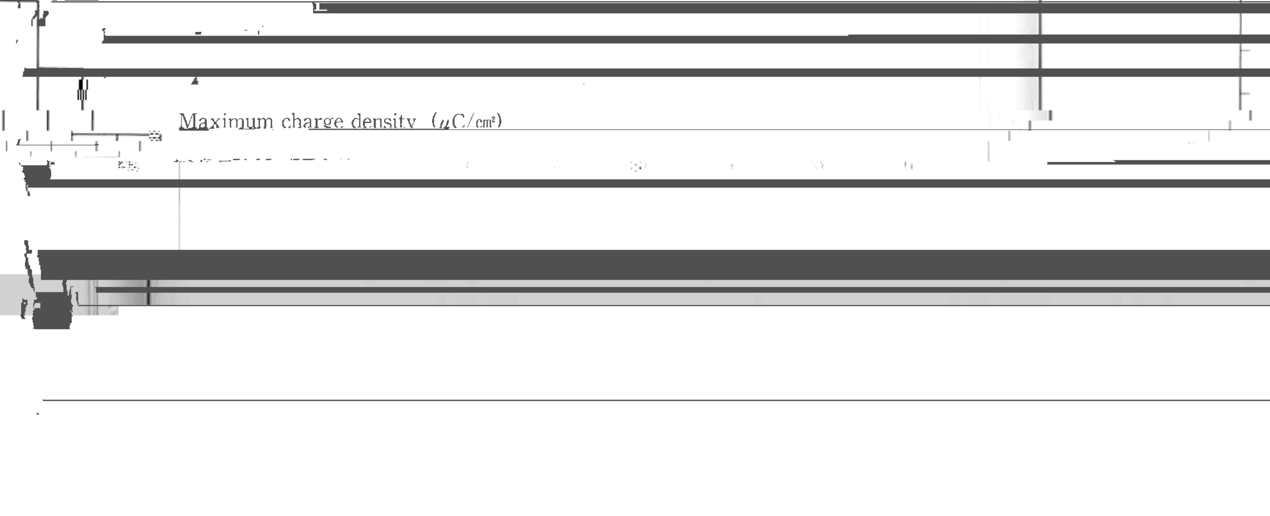
Sample	Si	Al	O	N	Y
A	[illegible]	2.9	11.6	48.0	1.5
B	33.6	3.2	16.4	45.5	1.4
C	35.5	3.2	14.4	45.5	1.4



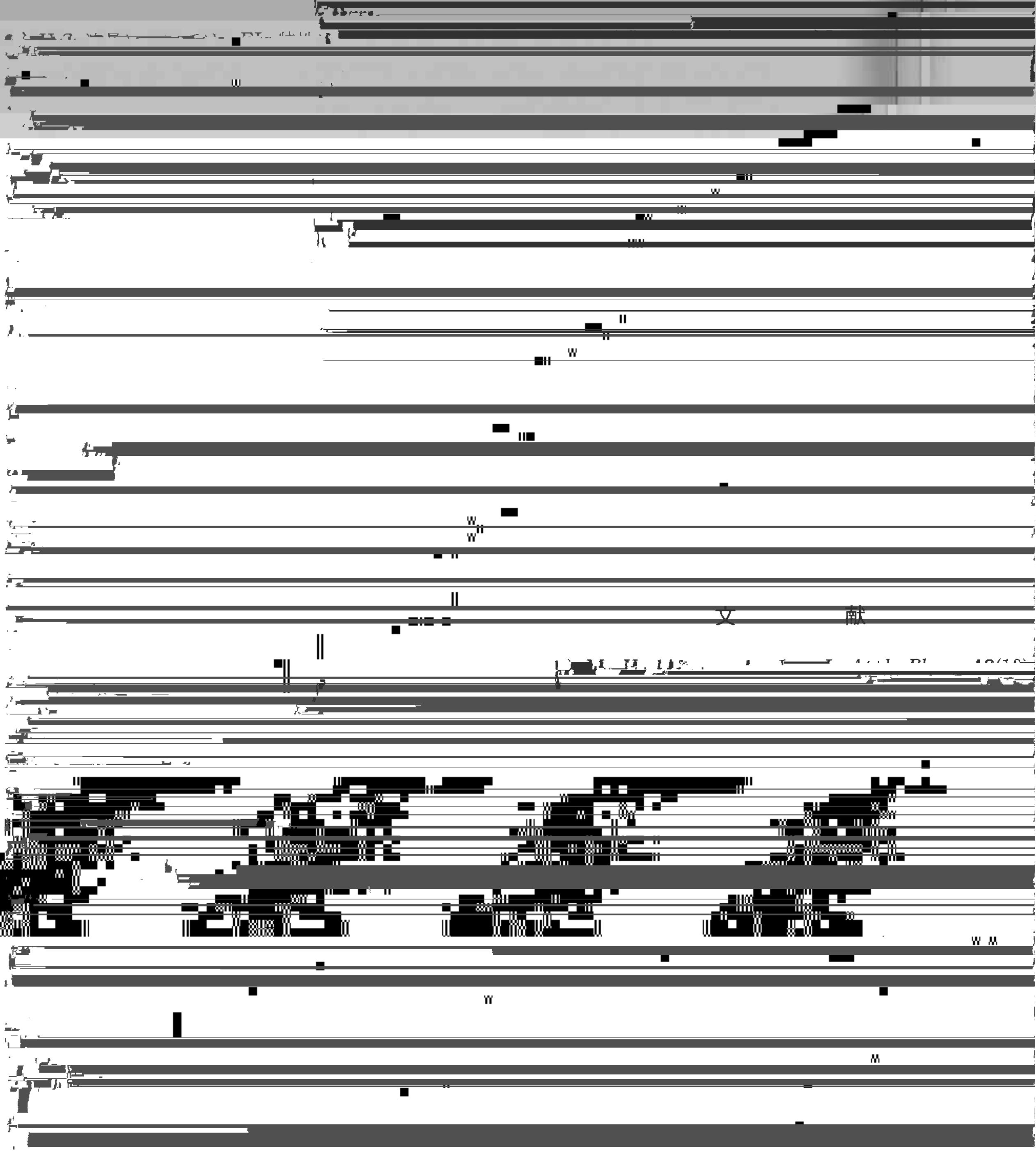





SiAlON
1000
Luminance
1KHz
Sine wave


8
6
Maximum charge density (μC/cm²)

10
6
130
150
170
190
210



文献